

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	641	257/528.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/23 10:25
S1	36784	circuit and gate and transistor and source and drain and resist\$4 and capacitor and diode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:16
S2	10798	S1 and (resist \$4 with voltage with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:17
S3	6843	S2 and (capacitor with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:18
S4	4249	S3 and (diode with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:18

S5	719	S4 and (PMOS or PMOSFET or (p-type adj MOSFET) or (p-type adj FET)) and (NMOS or NMOSFET or (n-type adj MOSFET) or (n-type adj FET))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:24
S6	319	S5 and (resist \$4 with (PMOS or PMOSFET or (p-type adj MOSFET) or (p-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:25
S7	273	S6 and (resist \$4 with (NMOS or NMOSFET or (n-type adj MOSFET) or (n-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:26
S8	127	S7 and (capacitor with (PMOS or PMOSFET or (p-type adj MOSFET) or (p-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:47
S9	138	S6 and (capacitor with (NMOS or NMOSFET or (n-type adj MOSFET) or (n-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:47

S10	92	S8 and (capacitor with (NMOS or NMOSFET or (n-type adj MOSFET) or (n-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:47
S11	67	S10 and (diode with (NMOS or NMOSFET or (n-type adj MOSFET) or (n-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:48
S12	59	S11 and (diode with (PMOS or PMOSFET or (p-type adj MOSFET) or (p-type adj FET)) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 09:48
S13	27	S12 and (driv \$3 with circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 10:15
S14	19	S13 and amplifier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 10:16
S15	14	S12 and (driv \$3 adj circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 10:23

S16	8	S14 and (voltage with source with (higher or lower))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 10:30
S17	3	S15 and (voltage with source with (higher or lower))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 10:30
S18	3	S15 and (voltage with source with (higher or lower))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 11:33
S19	696	257/499.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 12:01
S20	1048	257/335.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 12:58
S21	40656	(Ryoo or Jang).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 13:10
S22	231	S21 and circuit and diode and capacitor and resist\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 13:10
S23	38	S22 and gate and amplifier	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/05/22 13:11

5/23/08 10:25:42 AM

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